LM2705 Micropower Step-Up DC-DC Converter With 150-mA Peak Current Limit

1 Features
- 2.2-V to 7-V Input Range
- 150-mA, 0.7-Ω Internal Switch
- Adjustable Output Voltage up to 20 V
- Input Undervoltage Lockout
- 0.01-µA Shutdown Current
- Uses Small Surface-Mount Components
- Small 5-Pin SOT-23 Package

2 Applications
- LCD Bias Supplies
- White-LED Backlighting
- Handheld Devices
- Digital Cameras
- Portable Applications

3 Description
The LM2705 is a micropower step-up DC-DC converter in a small 5-pin SOT-23 package. A current-limited, fixed-off-time control scheme conserves operating current, which results in high efficiency over a wide range of load conditions. The 21-V switch allows for output voltages as high as 20 V. The low 400-ns off-time permits the use of tiny, low-profile inductors and capacitors to minimize footprint and cost in space-conscious portable applications. The LM2705 is ideal for LCD panels requiring low current and high efficiency as well as white-LED applications for cellular phone backlighting. The LM2705 device can drive up to 3 white LEDs from a single Li-Ion battery. The low peak-inductor current of the LM2705 makes it ideal for USB applications.

Device Information

<table>
<thead>
<tr>
<th>PART NUMBER</th>
<th>PACKAGE</th>
<th>BODY SIZE (NOM)</th>
</tr>
</thead>
<tbody>
<tr>
<td>LM2705</td>
<td>SOT-23 (5)</td>
<td>2.90 mm × 1.60 mm</td>
</tr>
</tbody>
</table>

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Typical 20-V Application

\[ V_{IN} = \text{Li-Ion} \]

\[ L = 68 \mu\text{H} \]

\[ D \]

\[ R1 = 510 \text{ k}\Omega \]

\[ R2 = 33 \text{ k}\Omega \]

\[ C_{IN} = 4.7 \mu\text{F} \]

\[ C_{OUT} = 1 \mu\text{F} \]

\[ 20 \text{ V} \]

\[ 6 \text{ mA} \]

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An IMPORTANT NOTICE at the end of this data sheet addresses availability, warranty, changes, use in safety-critical applications, intellectual property matters and other important disclaimers. PRODUCTION DATA.
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4 Revision History
NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision E (May 2013) to Revision F

• Added Device Information and Pin Configuration and Functions sections, ESD Ratings and Thermal Information tables, Feature Description, Device Functional Modes, Application and Implementation, Power Supply Recommendations, Layout, Device and Documentation Support, and Mechanical, Packaging, and Orderable Information sections ........................................................................................................................................... 1
• Deleted pin definition list - added content to Pin Functions .......................................................................................................................... 3
• Changed $R_{\text{θJA}}$ value from "220°C/W" to "164.9°C/W" ........................................................................................................................................... 4

Changes from Revision D (May 2013) to Revision E

• Changed layout of National Semiconductor data sheet to TI format ........................................................................................................... 14
5 Pin Configuration and Functions

### DBV Package
5-Pin SOT-23
Top View

<table>
<thead>
<tr>
<th>PIN NO.</th>
<th>NAME</th>
<th>TYPE</th>
<th>DESCRIPTION</th>
</tr>
</thead>
<tbody>
<tr>
<td>1</td>
<td>SW</td>
<td>Input</td>
<td>Power switch input. This is the drain of the internal NMOS power switch. Minimize the metal trace area connected to this pin to minimize EMI.</td>
</tr>
<tr>
<td>2</td>
<td>GND</td>
<td>—</td>
<td>Ground - tie directly to ground plane.</td>
</tr>
<tr>
<td>3</td>
<td>FB</td>
<td>Input</td>
<td>Output voltage feedback input — set the output voltage by selecting values for R1 and R2 using: R1 = R2 × (V_{OUT} / 1.237 V) −1</td>
</tr>
<tr>
<td>4</td>
<td>SHDN</td>
<td>Input</td>
<td>Active low shutdown - drive this pin to &gt; 1.1 V to enable the device. Drive this pin to &lt; 0.3 V to place the device in a low-power shutdown.</td>
</tr>
<tr>
<td>5</td>
<td>VIN</td>
<td>Input</td>
<td>Analog and power input supply pin</td>
</tr>
</tbody>
</table>
6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)

<table>
<thead>
<tr>
<th>Parameter</th>
<th>MIN</th>
<th>MAX</th>
<th>UNIT</th>
</tr>
</thead>
<tbody>
<tr>
<td>VIN</td>
<td>7.5</td>
<td>V</td>
<td></td>
</tr>
<tr>
<td>SW voltage</td>
<td>21</td>
<td>V</td>
<td></td>
</tr>
<tr>
<td>FB voltage</td>
<td>2</td>
<td>V</td>
<td></td>
</tr>
<tr>
<td>SHDN voltage</td>
<td>7.5</td>
<td>V</td>
<td></td>
</tr>
<tr>
<td>Maximum junction temperature, $T_J^{(3)}$</td>
<td>150</td>
<td>°C</td>
<td></td>
</tr>
<tr>
<td>Lead temperature</td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>Soldering (10 seconds)</td>
<td>300</td>
<td>°C</td>
<td></td>
</tr>
<tr>
<td>Vapor phase (60 seconds)</td>
<td>215</td>
<td>°C</td>
<td></td>
</tr>
<tr>
<td>Infrared (15 seconds)</td>
<td>220</td>
<td>°C</td>
<td></td>
</tr>
<tr>
<td>Storage temperature, $T_{stg}$</td>
<td>−65</td>
<td>150</td>
<td>°C</td>
</tr>
</tbody>
</table>

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) If Military/Aerospace specified devices are required, contact the TI Sales Office/Distributors for availability and specifications.

(3) The maximum allowable power dissipation is a function of the maximum junction temperature, $T_J^{(3)}$, the junction-to-ambient thermal resistance, $R_{JUA}$, and the ambient temperature, $T_A$. See Thermal Information for the thermal resistance. The maximum allowable power dissipation at any ambient temperature is calculated using: $P_{D(MAX)} = (T_J^{(3)} - T_A) / R_{JUA}$. Exceeding the maximum allowable power dissipation will cause excessive die temperature.

6.2 ESD Ratings

<table>
<thead>
<tr>
<th>Parameter</th>
<th>VALUE</th>
<th>UNIT</th>
</tr>
</thead>
<tbody>
<tr>
<td>$V_{(ESD)}$</td>
<td>±2000</td>
<td>V</td>
</tr>
<tr>
<td>Machine model</td>
<td>±200</td>
<td>V</td>
</tr>
</tbody>
</table>

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) ESD susceptibility using the machine model is 150 V for SW pin.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

<table>
<thead>
<tr>
<th>Parameter</th>
<th>MIN</th>
<th>NOM</th>
<th>MAX</th>
<th>UNIT</th>
</tr>
</thead>
<tbody>
<tr>
<td>Supply voltage</td>
<td>2.2</td>
<td>7</td>
<td>V</td>
<td></td>
</tr>
<tr>
<td>SW voltage, maximum</td>
<td></td>
<td>20.5</td>
<td>V</td>
<td></td>
</tr>
<tr>
<td>Junction temperature$^{(1)}$</td>
<td>−40</td>
<td>125</td>
<td>°C</td>
<td></td>
</tr>
</tbody>
</table>

(1) All limits specified at room temperature and at temperature extremes. All room temperature limits are 100% production tested or specified through statistical analysis. All limits at temperature extremes are specified via correlation using standard statistical quality control (SQC) methods. All limits are used to calculate average outgoing quality level (AOQL).

6.4 Thermal Information

<table>
<thead>
<tr>
<th>THERMAL METRIC$^{(1)}$</th>
<th>LM2705 DBV (SOT-23)</th>
<th>UNIT</th>
</tr>
</thead>
<tbody>
<tr>
<td>$R_{JUA}$ Junction-to-ambient thermal resistance</td>
<td>164.9</td>
<td>°C/W</td>
</tr>
<tr>
<td>$R_{JUC(top)}$ Junction-to-case (top) thermal resistance</td>
<td>116.8</td>
<td>°C/W</td>
</tr>
<tr>
<td>$R_{JUB}$ Junction-to-board thermal resistance</td>
<td>27.8</td>
<td>°C/W</td>
</tr>
<tr>
<td>$\psi_JT$ Junction-to-top characterization parameter</td>
<td>13.6</td>
<td>°C/W</td>
</tr>
<tr>
<td>$\psi_{JUB}$ Junction-to-board characterization parameter</td>
<td>27.3</td>
<td>°C/W</td>
</tr>
</tbody>
</table>

(1) For more information about traditional and new thermal metrics, see Semiconductor and IC Package Thermal Metrics.
## 6.5 Electrical Characteristics

Unless otherwise specified, specifications apply for $T_J = 25^\circ C$ and $V_{IN} = 2.2$ V.

<table>
<thead>
<tr>
<th>PARAMETER</th>
<th>TEST CONDITIONS</th>
<th>MIN$^{(1)}$</th>
<th>TYP$^{(2)}$</th>
<th>MAX$^{(1)}$</th>
<th>UNIT</th>
</tr>
</thead>
<tbody>
<tr>
<td>$I_Q$</td>
<td>Device disabled</td>
<td>40</td>
<td>70</td>
<td></td>
<td>µA</td>
</tr>
<tr>
<td></td>
<td>FB = 1.3 V</td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td></td>
<td>FB = 1.3 V, –40°C to 125°C</td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td></td>
<td>Device enabled</td>
<td>235</td>
<td>300</td>
<td></td>
<td></td>
</tr>
<tr>
<td></td>
<td>FB = 1.2 V</td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td></td>
<td>FB = 1.2 V, –40°C to 125°C</td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td></td>
<td>Shutdown</td>
<td>0.01</td>
<td>2.5</td>
<td></td>
<td></td>
</tr>
<tr>
<td></td>
<td>SHDN = 0 V</td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>$V_{FB}$</td>
<td>Feedback trip point</td>
<td>1.237</td>
<td></td>
<td></td>
<td>V</td>
</tr>
<tr>
<td></td>
<td>–40°C to 125°C</td>
<td>1.189</td>
<td>1.269</td>
<td></td>
<td></td>
</tr>
<tr>
<td>$I_{CL}$</td>
<td>Switch current limit</td>
<td>150</td>
<td>180</td>
<td></td>
<td>mA</td>
</tr>
<tr>
<td></td>
<td>–40°C to 125°C</td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>$I_B$</td>
<td>FB pin bias current</td>
<td>100</td>
<td>120</td>
<td></td>
<td>nA</td>
</tr>
<tr>
<td></td>
<td>FB = 1.23 V$^{(3)}$</td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td></td>
<td>FB = 1.23 V, –40°C to 125°C$^{(3)}$</td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>$V_{IN}$</td>
<td>Input voltage</td>
<td>2.2</td>
<td>7</td>
<td></td>
<td>V</td>
</tr>
<tr>
<td></td>
<td>–40°C to 125°C</td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>$R_{DS_ON}$</td>
<td>Switch $R_{DS_ON}$</td>
<td>0.7</td>
<td></td>
<td>1.6</td>
<td>Ω</td>
</tr>
<tr>
<td></td>
<td>–40°C to 125°C</td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>$T_{OFF}$</td>
<td>Switch off time</td>
<td>400</td>
<td></td>
<td></td>
<td>ns</td>
</tr>
<tr>
<td>$I_{SD}$</td>
<td>SHDN pin current</td>
<td>0</td>
<td>80</td>
<td></td>
<td>nA</td>
</tr>
<tr>
<td></td>
<td>SHDN = $V_{IN}$, $T_J = 25^\circ C$</td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td></td>
<td>SHDN = $V_{IN}$, $T_J = 125^\circ C$</td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td></td>
<td>SHDN = GND</td>
<td>15</td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>$I_L$</td>
<td>Switch leakage current</td>
<td>0.05</td>
<td>5</td>
<td></td>
<td>µA</td>
</tr>
<tr>
<td></td>
<td>$V_{SW} = 20$ V</td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>$V_{FB}$</td>
<td>Input undervoltage lockout</td>
<td>1.8</td>
<td></td>
<td></td>
<td>V</td>
</tr>
<tr>
<td>hysteresis</td>
<td>Feedback hysteresis</td>
<td>8</td>
<td></td>
<td></td>
<td>mV</td>
</tr>
<tr>
<td>$SHDN$ threshold</td>
<td>SHDN low</td>
<td>0.7</td>
<td></td>
<td>0.3</td>
<td>V</td>
</tr>
<tr>
<td></td>
<td>–40°C to 125°C</td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td></td>
<td>SHDN high</td>
<td>0.7</td>
<td></td>
<td>1.1</td>
<td></td>
</tr>
<tr>
<td></td>
<td>–40°C to 125°C</td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
</tbody>
</table>

$^{(1)}$ All limits specified at room temperature and at temperature extremes. All room temperature limits are 100% production tested or specified through statistical analysis. All limits at temperature extremes are specified via correlation using standard statistical quality control (SQC) methods. All limits are used to calculate average outgoing quality level (AOQL).

$^{(2)}$ Typical numbers are at 25°C and represent the most likely norm.

$^{(3)}$ Feedback current flows into the pin.
6.6 Typical Characteristics

Figure 1. Enable Current vs $V_{IN}$ (Device Switching)

Figure 2. Disable Current vs $V_{IN}$ (Device Not Switching)

Figure 3. SHDN Threshold vs $V_{IN}$

Figure 4. Switch Current Limit vs $V_{IN}$

Figure 5. Switch $R_{DSON}$ vs $V_{IN}$

Figure 6. FB Trip Point and FB Pin Current vs Temperature
Typical Characteristics (continued)

**Figure 7. Output Voltage vs Load Current**

- **V\text{OUT} = 20\text{V}**
- **V\text{IN} = 2.7\text{V}**
- **V\text{IN} = 3.3\text{V}**
- **V\text{IN} = 4.2\text{V}**

**Figure 8. Off Time vs Temperature**

**Figure 9. Step Response**

1) Load: 0.5 mA to 5 mA to 0.5 mA, DC
2) V\text{OUT}: 200 mV/div, AC
3. I\text{L}: 100 mA/div, DC

**Figure 10. Start-Up and Shutdown**

1. V\text{SW}: 20 V/div, DC
2. Inductor Current: 100 mA/div, DC
3. V\text{OUT}: 200 mV/div, AC

**Figure 11. Typical Switching Waveform**

1. V\text{SW}: 20 V/div, DC
2. Inductor Current: 100 mA/div, DC
3. V\text{OUT}: 200 mV/div, AC
7 Detailed Description

7.1 Overview
The LM2705 is a small boost converter utilizing a constant off-time architecture. The device can provide up to 20.5 V at the output with up to 150 mA of peak switch current.

7.2 Functional Block Diagram

7.3 Feature Description
The LM2705 device features a constant off-time control scheme. Operation can be best understood by referring to Functional Block Diagram and Figure 11. Transistors Q1 and Q2 and resistors R3 and R4 of Functional Block Diagram form a bandgap reference used to control the output voltage. When the voltage at the FB pin is less than 1.237 V, the Enable Comp in Functional Block Diagram enables the device, and the NMOS switch is turned on pulling the SW pin to ground. When the NMOS switch is on, current begins to flow through inductor L while the load current is supplied by the output capacitor C_{OUT}. Once the current in the inductor reaches the current limit, the CL comp trips, and the 400-ns one shot turns off the NMOS switch. The SW voltage then rises to the output voltage plus a diode drop, and the inductor current begins to decrease as shown in Figure 11. During this time the energy stored in the inductor is transferred to C_{OUT} and the load. After the 400-ns off-time the NMOS switch is turned on, and energy is stored in the inductor again. This energy transfer from the inductor to the output causes a stepping effect in the output ripple as shown in Figure 11.

This cycle is continued until the voltage at FB reaches 1.237 V. When FB reaches this voltage, the Enable Comp disables the device, turning off the NMOS switch and reducing the I_Q of the device to 40 µA. The load current is then supplied solely by C_{OUT} indicated by the gradually decreasing slope at the output as shown in Figure 11. When the FB pin drops slightly below 1.237 V, the Enable Comp enables the device and begins the cycle described previously.

7.4 Device Functional Modes
The SHDN pin can be used to turn off the LM2705 and reduce the I_Q to 0.01 µA. In shutdown mode the output voltage is a diode drop lower than the input voltage.
8 Application and Implementation

NOTE
Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI’s customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information
The LM2705 is a 20-V boost designed for low power boost applications. Typical input voltage range makes this ideal for standard single cell Li+ batteries or 2 to 4 series alkaline batteries.

8.2 Typical Application
Figure 12 shows a typical Li+ voltage range to 20-V application. The 68-µH inductor allows for a low ripple current and high light-load efficiency.

Figure 12. Typical 20-V Application

8.2.1 Design Requirements
For typical DC-DC converter applications, use the parameters listed in Table 1.

<table>
<thead>
<tr>
<th>DESIGN PARAMETER</th>
<th>EXAMPLE VALUE</th>
</tr>
</thead>
<tbody>
<tr>
<td>Input voltage</td>
<td>2.5 V to 4.2 V</td>
</tr>
<tr>
<td>Output voltage</td>
<td>12 V</td>
</tr>
<tr>
<td>Output current</td>
<td>up to 8 mA</td>
</tr>
<tr>
<td>Inductor</td>
<td>33 µH</td>
</tr>
</tbody>
</table>

8.2.2 Detailed Design Procedure

8.2.2.1 Inductor Selection - Boost Regulator
The appropriate inductor for a given application is calculated using Equation 1:

\[ L = \left( \frac{V_{OUT} - V_{IN(min)} + V_D}{I_{CL}} \right) T_{OFF} \]

where
- \( V_D \) is the Schottky diode voltage
- \( I_{CL} \) is the switch current limit found in the Typical Characteristics
8.2.2 Inductor Selection - SEPIC Regulator

The boost inductor, L1, can be smaller or larger but is generally chosen to be the same value as L2. See Figure 23 and Figure 24 for typical SEPIC applications.

8.2.2.3 Diode Selection

To maintain high efficiency, the average current rating of the Schottky diode should be larger than the peak inductor current, IpK. Schottky diodes with a low forward drop and fast switching speeds are ideal for increasing efficiency in portable applications. Choose a reverse breakdown of the Schottky diode larger than the output voltage.

8.2.2.4 Capacitor Selection

Choose low equivalent series resistance (ESR) capacitors for the output to minimize output voltage ripple. Multilayer ceramic capacitors are the best choice. For most applications, a 1-µF ceramic capacitor is sufficient. For some applications a reduction in output voltage ripple can be achieved by increasing the output capacitor. Output voltage ripple can further be reduced by adding a 4.7-pF feed-forward capacitor in the feedback network placed in parallel with RF1 (see Functional Block Diagram).

Local bypassing for the input is needed on the LM2705. Multilayer ceramic capacitors are a good choice for this as well. A 4.7-µF capacitor is sufficient for most applications. For additional bypassing, a 100-nF ceramic capacitor can be used to shunt high frequency ripple on the input.
8.2.3 Application Curves

**Figure 13. Efficiency vs Load Current**

- $V_{OUT} = 20V$
- $V_{IN} = 4.2V$
- $V_{IN} = 3.3V$
- $V_{IN} = 2.7V$

**Figure 14. Efficiency vs Load Current**

- $V_{OUT} = 12V$
- $V_{IN} = 5.0V$
- $V_{IN} = 4.2V$
- $V_{IN} = 2.5V$

**Figure 15. Output Ripple Voltage**

- $V_{SW}$
- $I_L$
- $V_{OUT}$
- $I_{OUT} = 0.5mA$
- $V_{IN} = 3.6V$
- $V_{OUT} = 18V$
- TIME (4 $\mu$s/DIV)

**Figure 16. Output Ripple Voltage**

- $V_{SW}$
- $I_L$
- $V_{OUT}$
- $I_{OUT} = 0.5mA$
- $V_{IN} = 3.6V$
- $V_{OUT} = 18V$
- TIME (10 $\mu$s/DIV)

**Figure 17. Two White-LED Efficiency**

**Figure 18. Three White-LED Efficiency**
8.3 Additional Applications

Figure 19. Two White-LED Application

Figure 20. Three White-LED Application
Additional Applications (continued)

Figure 21. Li-Ion 12-V Application

Figure 22. 5-V to 12-V Application
Additional Applications (continued)

**Figure 23. 3.3-V SEPIC Application**

**Figure 24. 5-V SEPIC Application**
9 Power Supply Recommendations

The LM2705 is designed to operate from an input voltage supply range from 2.2 V to 7 V. This input supply must be well regulated and capable to supply the required input current. If the input supply is located far from the LM2705, additional bulk capacitance may be required in addition to the ceramic bypass capacitors.

10 Layout

10.1 Layout Guidelines

The input bypass capacitor $C_{IN}$, as shown in Figure 25, must be placed close to the device. This reduces copper trace resistance, which effects input voltage ripple of the LM2705 device. For additional input voltage filtering, a 100-nF bypass capacitor can be placed in parallel with $C_{IN}$ to shunt any high frequency noise to ground. The output capacitor, $C_{OUT}$, must also be placed close to the device. Any copper trace connections for the $C_{OUT}$ capacitor can increase the series resistance, which directly effects output voltage ripple. Keep the feedback network, resistors R1 and R2, close to the FB pin to minimize copper trace connections that can inject noise into the system. The ground connection for the feedback resistor network must connect directly to an analog ground plane. Tie the analog ground plane directly to the GND pin. If no analog ground plane is available, the ground connection for the feedback network must tie directly to the GND pin. Minimize trace connections made to the inductor and Schottky diode to reduce power dissipation and increase overall efficiency.

10.2 Layout Example

![Figure 25. LM2705 Layout Example](image-url)
11 Device and Documentation Support

11.1 Device Support

11.1.1 Third-Party Products Disclaimer
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11.2 Receiving Notification of Documentation Updates
To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper
right corner, click on Alert me to register and receive a weekly digest of any product information that has
changed. For change details, review the revision history included in any revised document.

11.3 Community Resources
The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective
contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of
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**TI E2E™ Online Community** TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration
among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help
solve problems with fellow engineers.

**Design Support** TI's Design Support Quickly find helpful E2E forums along with design support tools and
contact information for technical support.

11.4 Trademarks
E2E is a trademark of Texas Instruments.
All other trademarks are the property of their respective owners.

11.5 Electrostatic Discharge Caution
These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam
during storage or handling to prevent electrostatic damage to the MOS gates.

11.6 Glossary
SLYZ022 — TI Glossary.
This glossary lists and explains terms, acronyms, and definitions.

12 Mechanical, Packaging, and Orderable Information
The following pages include mechanical, packaging, and orderable information. This information is the most
current data available for the designated devices. This data is subject to change without notice and revision of
this document. For browser-based versions of this data sheet, refer to the left-hand navigation.
## Packaging Information

<table>
<thead>
<tr>
<th>Orderable Device</th>
<th>Status</th>
<th>Package Type</th>
<th>Package Drawing</th>
<th>Pins</th>
<th>Package Qty</th>
<th>Eco Plan</th>
<th>Lead finish/Ball material</th>
<th>MSL Peak Temp</th>
<th>Op Temp (°C)</th>
<th>Device Marking</th>
<th>Samples</th>
</tr>
</thead>
<tbody>
<tr>
<td>LM2705MF-ADJ/NOPB</td>
<td>ACTIVE</td>
<td>SOT-23</td>
<td>DBV</td>
<td>5</td>
<td>1000</td>
<td>RoHS &amp; Green</td>
<td>SN</td>
<td>Level-1-260C-UNLIM</td>
<td>-40 to 85</td>
<td>S59B</td>
<td>Samples</td>
</tr>
<tr>
<td>LM2705MFX-ADJ/NOPB</td>
<td>ACTIVE</td>
<td>SOT-23</td>
<td>DBV</td>
<td>5</td>
<td>3000</td>
<td>RoHS &amp; Green</td>
<td>SN</td>
<td>Level-1-260C-UNLIM</td>
<td>-40 to 85</td>
<td>S59B</td>
<td>Samples</td>
</tr>
</tbody>
</table>

(1) The marketing status values are defined as follows:
- **ACTIVE:** Product device recommended for new designs.
- **LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
- **NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
- **PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.
- **OBSOLETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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TAPE AND REEL INFORMATION

<table>
<thead>
<tr>
<th>Device</th>
<th>Package Type</th>
<th>Package Drawing</th>
<th>Pins</th>
<th>SPQ</th>
<th>Reel Diameter (mm)</th>
<th>Reel Width W1 (mm)</th>
<th>A0 (mm)</th>
<th>B0 (mm)</th>
<th>K0 (mm)</th>
<th>P1 (mm)</th>
<th>W (mm)</th>
<th>Pin1 Quadrant</th>
</tr>
</thead>
<tbody>
<tr>
<td>LM2705MF-ADJ/NOPB</td>
<td>SOT-23</td>
<td>DBV</td>
<td>5</td>
<td>1000</td>
<td>178.0</td>
<td>8.4</td>
<td>3.2</td>
<td>3.2</td>
<td>1.4</td>
<td>4.0</td>
<td>8.0</td>
<td>Q3</td>
</tr>
<tr>
<td>LM2705MFX-ADJ/NOPB</td>
<td>SOT-23</td>
<td>DBV</td>
<td>5</td>
<td>3000</td>
<td>178.0</td>
<td>8.4</td>
<td>3.2</td>
<td>3.2</td>
<td>1.4</td>
<td>4.0</td>
<td>8.0</td>
<td>Q3</td>
</tr>
</tbody>
</table>

*All dimensions are nominal.*

- **A0**: Dimension designed to accommodate the component width
- **B0**: Dimension designed to accommodate the component length
- **K0**: Dimension designed to accommodate the component thickness
- **W**: Overall width of the carrier tape
- **P1**: Pitch between successive cavity centers
**PACKAGE MATERIALS INFORMATION**

**TAPE AND REEL BOX DIMENSIONS**

<table>
<thead>
<tr>
<th>Device</th>
<th>Package Type</th>
<th>Package Drawing</th>
<th>Pins</th>
<th>SPQ</th>
<th>Length (mm)</th>
<th>Width (mm)</th>
<th>Height (mm)</th>
</tr>
</thead>
<tbody>
<tr>
<td>LM2705MF-ADJ/NOPB</td>
<td>SOT-23</td>
<td>DBV</td>
<td>5</td>
<td>1000</td>
<td>210.0</td>
<td>185.0</td>
<td>35.0</td>
</tr>
<tr>
<td>LM2705MFX-ADJ/NOPB</td>
<td>SOT-23</td>
<td>DBV</td>
<td>5</td>
<td>3000</td>
<td>210.0</td>
<td>185.0</td>
<td>35.0</td>
</tr>
</tbody>
</table>

*All dimensions are nominal
NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
5. Publication IPC-7351 may have alternate designs.
6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.
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